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PHY-503

Solid State Physics

M. Sc. PHYSICS (MSCPHY-12/13/16)

First Year, Examination, 2017

Time: 3 Hours Max. Marks: 70

Note: This paper is of seventy (70) marks containing three (03) sections A, B and C. Learners are required to attempt the questions contained in these sections according to the detailed instructions given therein.

Section-A

(Long Answer Type Questions)

Note: Section 'A' contains four (04) long answer type questions of fifteen (15) marks each. Learners are required to answer *two* (02) questions only.

- 1. Show that the reciprocal lattice of a hexagonal lattice is a hexagonal lattice with a rotation of axis.
- 2. Explain the lattice dynamics of monoatomic twodimensional lattices.
- 3. There are N atoms in a metal crystal and N_i interstitials in its structure. If \bar{E} and n are the average energy required to create one Frenkel defect and equilibrium number of defects respectively, then show that :

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$$n = N/N_i^{1/2} \exp\left(-\frac{\overline{E}}{2k_BT}\right)$$

where $k_{\rm B}$ is Boltzmann constant.

4. Give the quantum theory of paramagnetism and explain how it removes that shortcoming of Langevin's theory.

Section-B

(Short Answer Type Questions)

Note: Section 'B' contains eight (08) short answer type questions of five (05) marks each. Learners are required to answer *six* (06) questions only.

- 1. With the help of diagram, calculate the packing fraction of a face centred cubic (fcc) structure.
- 2. Obtain the reciprocal lattice to a FCC lattice.
- 3. Explain Grain boundaries.
- 4. Give the limitation of Debye model.
- 5. In an intrinsic semiconductor, the effective mass of electron is $0.07 m_e$ and that of hole is $0.4 m_e$, where m_e is the rest mass of electron. Calculate the intrinsic carrier concentration at 300 K.

Given that
$$E_g = 0.7 \text{ eV}$$
, $k_B = 1.38 \times 10^{-23} \text{ J/K}$, $h = 6.67 \times 10^{-34} \text{ Js}$, $m_e = 9.1 \times 10^{-31} \text{ kg}$, $T = 300 \text{ K}$

- 6. What are Debye frequency and Debye temperature? Give its physical significance.
- 7. The intrinsic carrier density of Ge at 27° C is 2.4×10^{17} m⁻³. Calculate its intrinsic resistivity, if the electron and hole mobilities are 0.35 m² V⁻¹ s⁻¹ and 0.18 m² V⁻¹ s⁻¹.

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8. What is piezoelectricity? Give the application of piezoelectricity.

Section-C

(Objective Type Questions)

Note: Section 'C' contains ten (10) objective type questions of one (01) mark each. All the questions of this section are compulsory.

- 1. The Bravais lattice, formed by all points with Cartesian co-ordinates (n_1, n_2, n_3) , where n_1, n_2, n_3 are either all odd or all even is:
 - (a) Simple cubic
 - (b) Body centered cubic
 - (c) Face centered cubic
 - (d) Hexagonal close packed
- 2. The nearest neighbour distance in a bcc structure with lattice constant *a* is :
 - (a) *a*
 - (b) $a / \sqrt{2}$
 - (c) $a\sqrt{3}/2$
 - (d) $\sqrt{3} / 4a$
- 3. X-ray of wavelength 10 picometer are scattered from a target. The maximum wavelength present in the scattered X-rays is:
 - (a) 10 picometer

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- (b) 12.426 picometer
- (c) 14.852 picometer
- (d) not determined
- 4. Soft mode:
 - (a) occurs in acoustical branch only
 - (b) occurs in optical branch when the frequency dips to almost zero
 - (c) occurs in alkali halides
 - (d) does not occur in ferroelectric materials
- 5. In an Umklapp process:
 - (a) there is no conservation of momentum of the system electron plus phonon
 - (b) there is conservation of momentum of the system electrons plus plus phonon
 - (c) an electron does not absorb a phonon
 - (d) an electron does not arrive in a state at boundary of a Brillouin zone whereupon it suffers a reflection
- 6. At temperatures above absolute zero, for $E \ll E_F$, the Fermi-Dirac function approaches :
 - (a) $e^{-E/kT}$
 - (b) zero
 - (c) unit
 - (d) infinity
- 7. The effective mass of an electron:
 - (a) can never be negative
 - (b) can never be infinity
 - (c) depends on its effective charge only
 - (d) can be positive, negative as well as infinity

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- 8. In n type semiconductor, the position of Fermi level :
 - (a) is lower than the centre of energy gap
 - (b) at the centre of energy gap
 - (c) is higher than the centre of energy gap
 - (d) can be any where depending upon the doping concentration
- 9. The Hall effects occurs in:
 - (a) metals only
 - (b) *n*-type semiconductors only
 - (c) intrinsic semiconductors only
 - (d) All of the above
- 10. The electronic polarizability, at moderate temperature is:
 - (a) linearly depending on temperature
 - (b) independent of temperature
 - (c) inversely depending on temperature
 - (d) inversely depending on square of temperature

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